

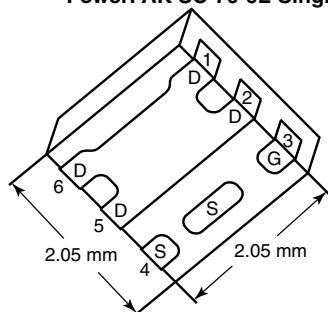


## P-Channel 12 V (D-S) MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) (Max.) | $I_D$ (A)         | $Q_g$ (Typ.) |
|--------------|----------------------------------|-------------------|--------------|
| - 12         | 0.0135 at $V_{GS} = -4.5$ V      | - 12 <sup>a</sup> | 31 nC        |
|              | 0.0194 at $V_{GS} = -2.5$ V      | - 12 <sup>a</sup> |              |
|              | 0.0344 at $V_{GS} = -1.8$ V      | - 12 <sup>a</sup> |              |
|              | 0.0710 at $V_{GS} = -1.5$ V      | - 3               |              |

PowerPAK SC-70-6L-Single



## Ordering Information:

SiA447DJ-T4-GE3 (Lead (Pb)-free and Halogen-free)

SiA447DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

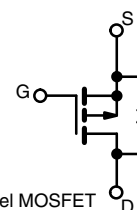
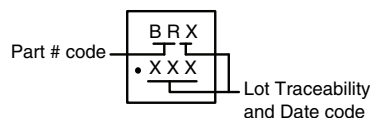
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 %  $R_g$  Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Providing low voltage drop in Smart Phones, Tablet PCs, Mobile Computing:
  - Battery Switches
  - Battery Management
  - Load Switches

### Marking Code



P-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

| Parameter                                                    | Symbol         | Limit                                               | Unit             |
|--------------------------------------------------------------|----------------|-----------------------------------------------------|------------------|
| Drain-Source Voltage                                         | $V_{DS}$       | - 12                                                | V                |
| Gate-Source Voltage                                          | $V_{GS}$       | $\pm 8$                                             |                  |
| Continuous Drain Current ( $T_J = 150^\circ\text{C}$ )       | $I_D$          | $T_C = 25^\circ\text{C}$<br>- 12 <sup>a</sup>       | A                |
|                                                              |                | $T_C = 70^\circ\text{C}$<br>- 12 <sup>a</sup>       |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$<br>- 12 <sup>a, b, c</sup> |                  |
|                                                              |                | $T_A = 70^\circ\text{C}$<br>- 10 <sup>b, c</sup>    |                  |
| Pulsed Drain Current ( $t = 300 \mu\text{s}$ )               | $I_{DM}$       | - 50                                                |                  |
| Continuous Source-Drain Diode Current                        | $I_S$          | $T_C = 25^\circ\text{C}$<br>- 12 <sup>a</sup>       |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$<br>- 2.9 <sup>b, c</sup>   |                  |
| Maximum Power Dissipation                                    | $P_D$          | $T_C = 25^\circ\text{C}$<br>19                      | W                |
|                                                              |                | $T_C = 70^\circ\text{C}$<br>12                      |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$<br>3.5 <sup>b, c</sup>     |                  |
|                                                              |                | $T_A = 70^\circ\text{C}$<br>2.2 <sup>b, c</sup>     |                  |
| Operating Junction and Storage Temperature Range             | $T_J, T_{stg}$ | - 55 to 150                                         | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) <sup>d, e</sup> |                | 260                                                 |                  |

### THERMAL RESISTANCE RATINGS

| Parameter                                   |              | Symbol     | Typical | Maximum | Unit               |
|---------------------------------------------|--------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient <sup>b, f</sup> | $t \leq 5$ s | $R_{thJA}$ | 28      | 36      | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case (Drain)            | Steady State | $R_{thJC}$ | 5.3     | 6.5     |                    |

## Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$  s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is  $80^\circ\text{C/W}$ .

## SiA447DJ

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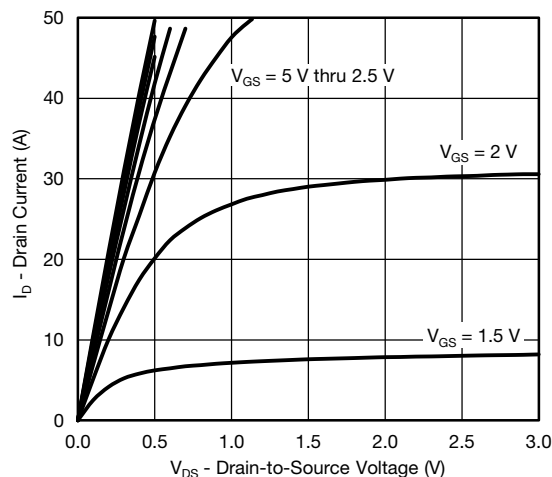
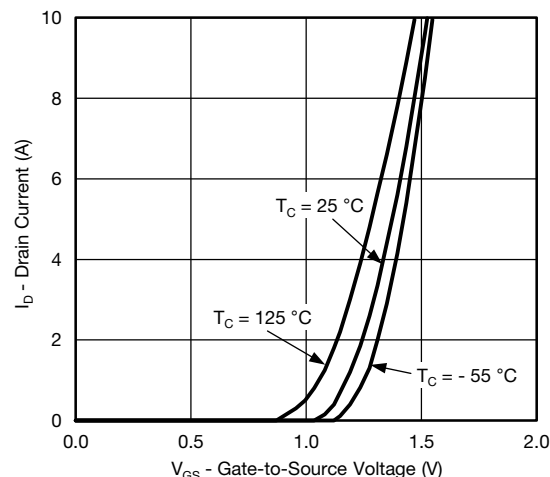
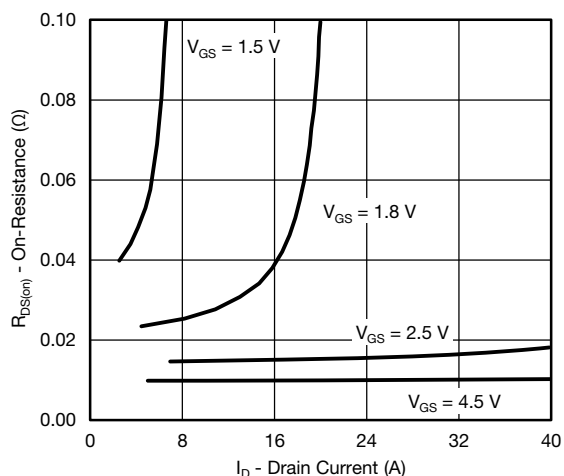
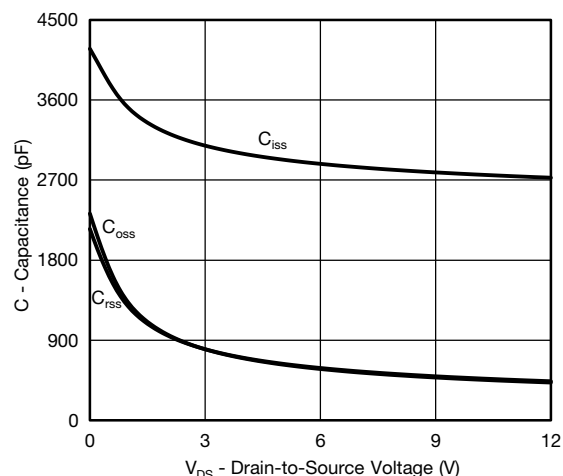
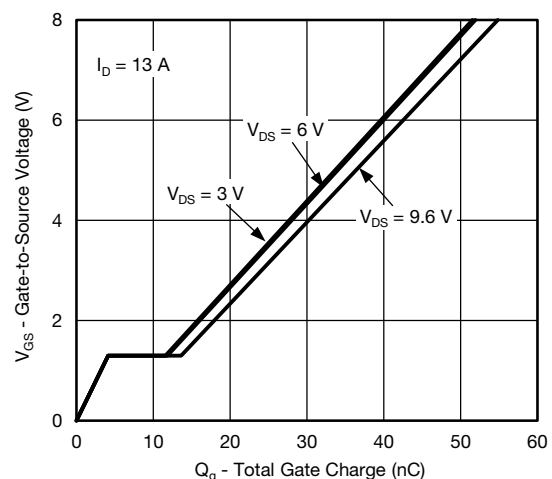
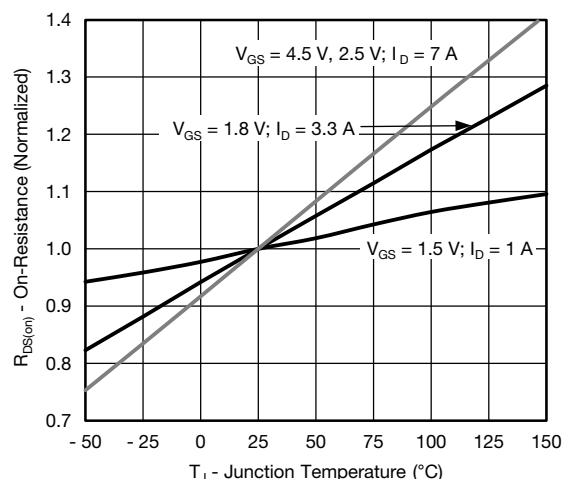
| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                      |                                                                                                                              |       |        |        |       |  |
|-----------------------------------------------------------------|--------------------------------------|------------------------------------------------------------------------------------------------------------------------------|-------|--------|--------|-------|--|
| Parameter                                                       | Symbol                               | Test Conditions                                                                                                              | Min.  | Typ.   | Max.   | Unit  |  |
| Static                                                          |                                      |                                                                                                                              |       |        |        |       |  |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>                      | V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA                                                                               | - 12  |        |        | V     |  |
| V <sub>DS</sub> Temperature Coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = - 250 μA                                                                                                    |       | - 7    |        | mV/°C |  |
| V <sub>GS(th)</sub> Temperature Coefficient                     | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |                                                                                                                              |       | 3      |        |       |  |
| Gate-Source Threshold Voltage                                   | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA                                                                | - 0.4 |        | - 0.85 | V     |  |
| Gate-Source Leakage                                             | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V                                                                               |       |        | ± 100  | nA    |  |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>                     | V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V                                                                              |       |        | - 1    | μA    |  |
|                                                                 |                                      | V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                      |       |        | - 10   |       |  |
| On-State Drain Current <sup>a</sup>                             | I <sub>D(on)</sub>                   | V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 4.5 V                                                                           | - 10  |        |        | A     |  |
| Drain-Source On-State Resistance <sup>a</sup>                   | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 7 A                                                                            |       | 0.0110 | 0.0135 | Ω     |  |
|                                                                 |                                      | V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 5 A                                                                            |       | 0.0150 | 0.0194 |       |  |
|                                                                 |                                      | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 3 A                                                                            |       | 0.0230 | 0.0344 |       |  |
|                                                                 |                                      | V <sub>GS</sub> = - 1.5 V, I <sub>D</sub> = - 1 A                                                                            |       | 0.0400 | 0.0710 |       |  |
| Forward Transconductance <sup>a</sup>                           | g <sub>fs</sub>                      | V <sub>DS</sub> = - 6 V, I <sub>D</sub> = - 7 A                                                                              |       | 35     |        | S     |  |
| Dynamic <sup>b</sup>                                            |                                      |                                                                                                                              |       |        |        |       |  |
| Input Capacitance                                               | C <sub>iss</sub>                     | V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                                    |       | 2880   |        | pF    |  |
| Output Capacitance                                              | C <sub>oss</sub>                     |                                                                                                                              |       | 590    |        |       |  |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>                     |                                                                                                                              |       | 585    |        |       |  |
| Total Gate Charge                                               | Q <sub>g</sub>                       | V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = - 8 V, I <sub>D</sub> = - 13 A                                                    |       | 52     | 80     | nC    |  |
|                                                                 |                                      | V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 13 A                                                  |       | 31     | 47     |       |  |
|                                                                 |                                      |                                                                                                                              |       |        | 4.2    |       |  |
|                                                                 |                                      |                                                                                                                              |       |        | 7.8    |       |  |
| Gate-Source Charge                                              | Q <sub>gs</sub>                      |                                                                                                                              |       |        |        |       |  |
| Gate-Drain Charge                                               | Q <sub>gd</sub>                      |                                                                                                                              |       |        |        |       |  |
| Gate Resistance                                                 | R <sub>g</sub>                       | f = 1 MHz                                                                                                                    | 0.8   | 4.3    | 8.6    | Ω     |  |
| Turn-On Delay Time                                              | t <sub>d(on)</sub>                   | V <sub>DD</sub> = - 6 V, R <sub>L</sub> = 0.6 Ω<br>I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω |       | 30     | 60     | ns    |  |
| Rise Time                                                       | t <sub>r</sub>                       |                                                                                                                              |       | 30     | 60     |       |  |
| Turn-Off Delay Time                                             | t <sub>d(off)</sub>                  |                                                                                                                              |       | 60     | 120    |       |  |
| Fall Time                                                       | t <sub>f</sub>                       |                                                                                                                              |       | 25     | 50     |       |  |
| Turn-On Delay Time                                              | t <sub>d(on)</sub>                   | V <sub>DD</sub> = - 6 V, R <sub>L</sub> = 0.6 Ω<br>I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 8 V, R <sub>g</sub> = 1 Ω   |       | 12     | 25     |       |  |
| Rise Time                                                       | t <sub>r</sub>                       |                                                                                                                              |       | 10     | 20     |       |  |
| Turn-Off Delay Time                                             | t <sub>d(off)</sub>                  |                                                                                                                              |       | 65     | 130    |       |  |
| Fall Time                                                       | t <sub>f</sub>                       |                                                                                                                              |       | 20     | 40     |       |  |
| Drain-Source Body Diode Characteristics                         |                                      |                                                                                                                              |       |        |        |       |  |
| Continuous Source-Drain Diode Current                           | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C                                                                                                       |       |        | - 12   | A     |  |
| Pulse Diode Forward Current                                     | I <sub>SM</sub>                      |                                                                                                                              |       |        | - 50   |       |  |
| Body Diode Voltage                                              | V <sub>SD</sub>                      | I <sub>S</sub> = - 10 A, V <sub>GS</sub> = 0                                                                                 |       | - 0.8  | - 1.2  | V     |  |
| Body Diode Reverse Recovery Time                                | t <sub>rr</sub>                      | I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C                                                            |       | 25     | 50     | ns    |  |
| Body Diode Reverse Recovery Charge                              | Q <sub>rr</sub>                      |                                                                                                                              |       | 7.5    | 15     | nC    |  |
| Reverse Recovery Fall Time                                      | t <sub>a</sub>                       |                                                                                                                              |       | 8      |        | ns    |  |
| Reverse Recovery Rise Time                                      | t <sub>b</sub>                       |                                                                                                                              |       | 17     |        |       |  |

Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

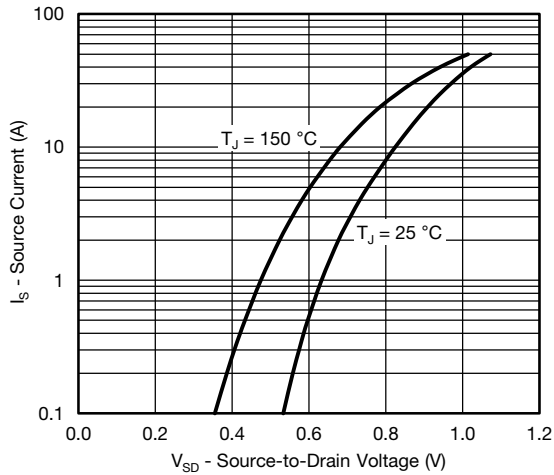
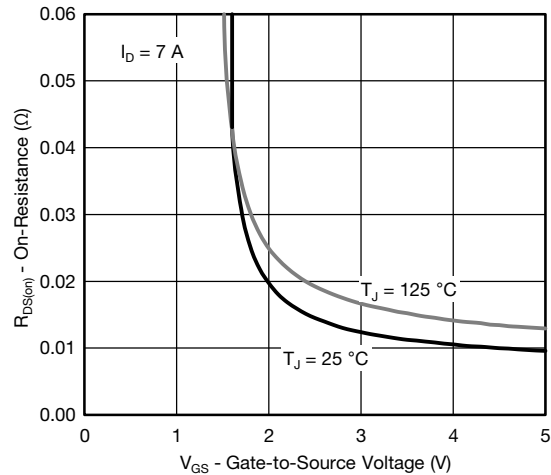
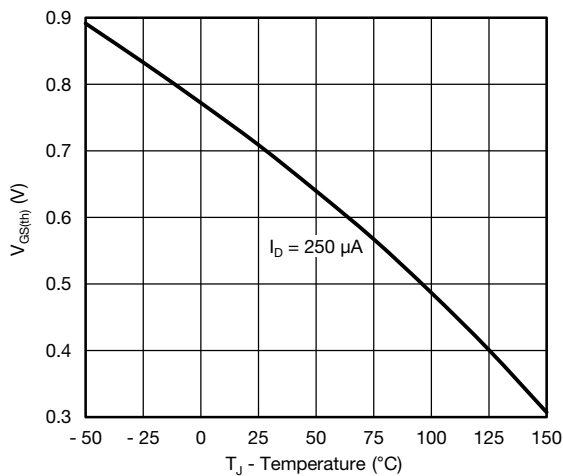
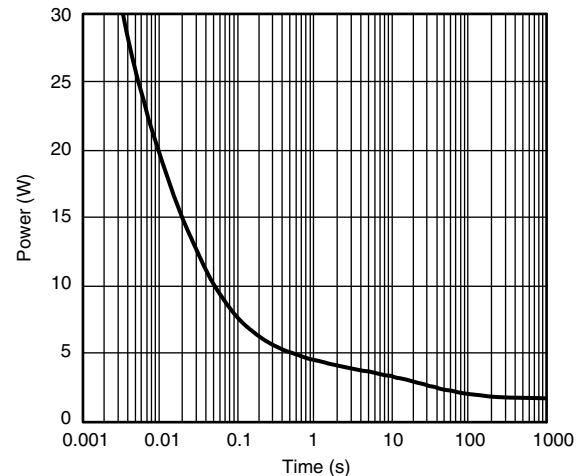
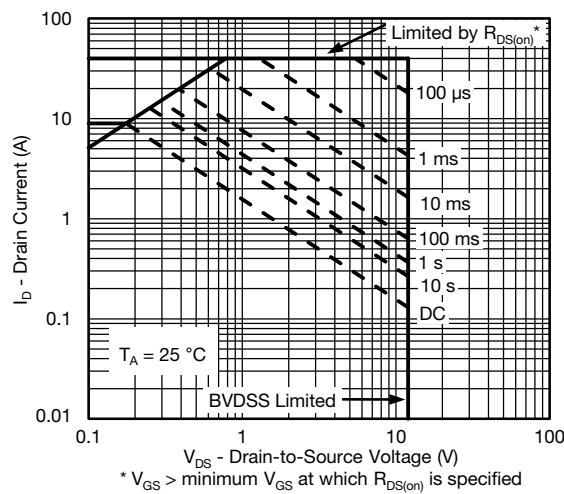
b. Guaranteed by design, not subject to production testing.

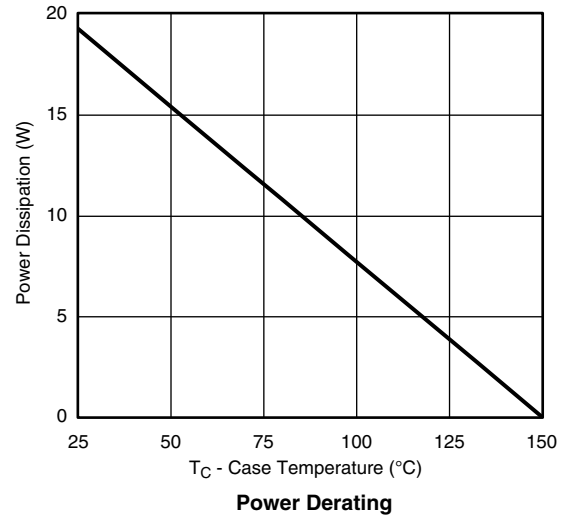
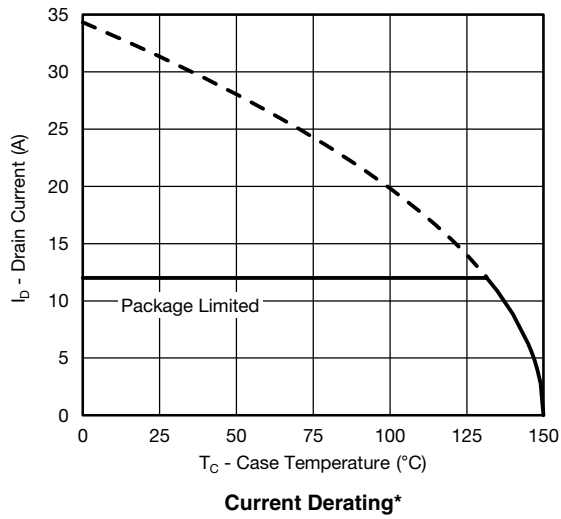
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current and Gate Voltage**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**SiA447DJ**

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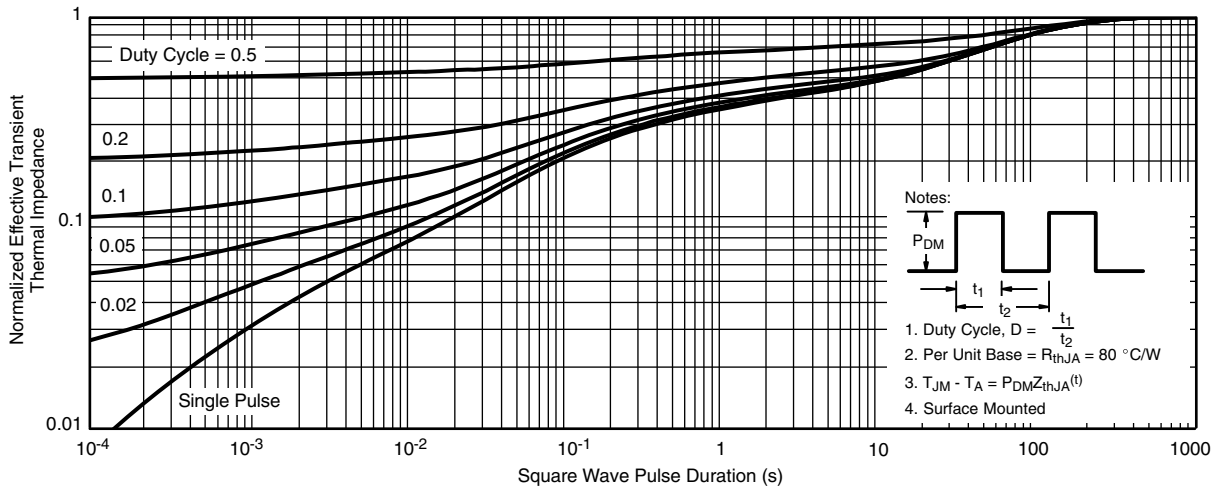
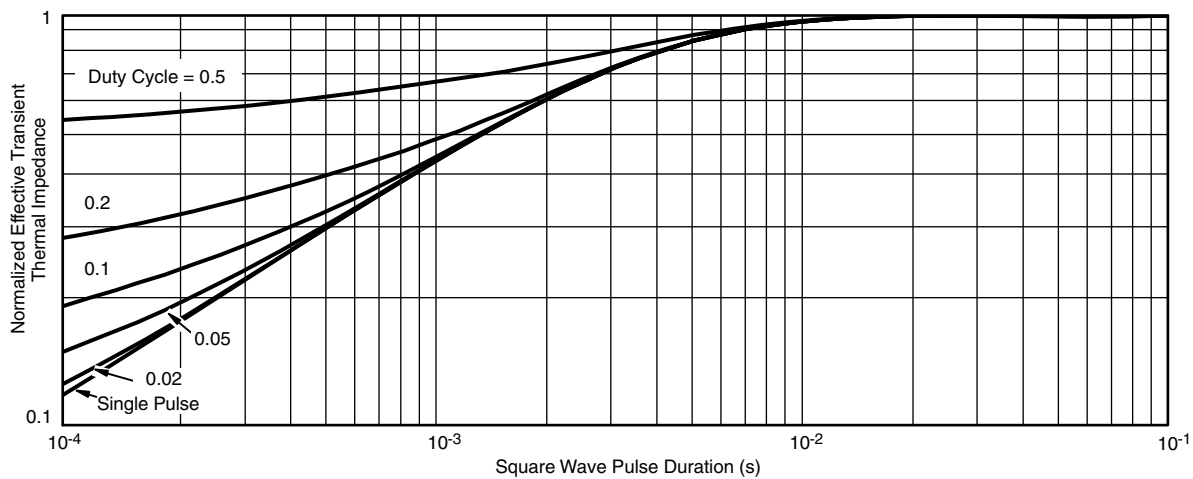
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Safe Operating Area, Junction-to-Ambient**


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**SiA447DJ**

Vishay Siliconix

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?63774](http://www.vishay.com/ppg?63774).



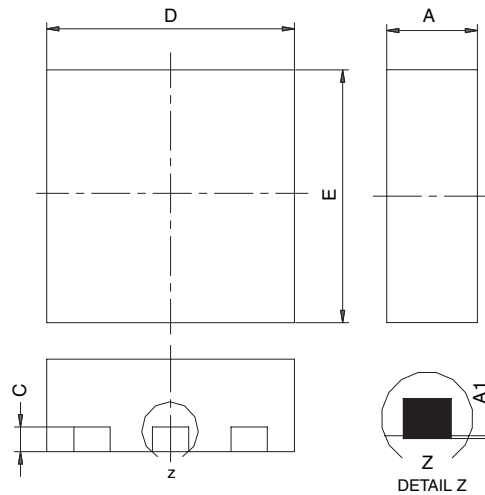
## PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE



BACKSIDE VIEW OF DUAL



### Notes:

1. All dimensions are in millimeters
2. Package outline exclusive of mold flash and metal burr
3. Package outline inclusive of plating

| DIM                                           | SINGLE PAD  |       |       |           |       |       | DUAL PAD    |       |       |           |       |       |
|-----------------------------------------------|-------------|-------|-------|-----------|-------|-------|-------------|-------|-------|-----------|-------|-------|
|                                               | MILLIMETERS |       |       | INCHES    |       |       | MILLIMETERS |       |       | INCHES    |       |       |
|                                               | Min         | Nom   | Max   | Min       | Nom   | Max   | Min         | Nom   | Max   | Min       | Nom   | Max   |
| A                                             | 0.675       | 0.75  | 0.80  | 0.027     | 0.030 | 0.032 | 0.675       | 0.75  | 0.80  | 0.027     | 0.030 | 0.032 |
| A1                                            | 0           | -     | 0.05  | 0         | -     | 0.002 | 0           | -     | 0.05  | 0         | -     | 0.002 |
| b                                             | 0.23        | 0.30  | 0.38  | 0.009     | 0.012 | 0.015 | 0.23        | 0.30  | 0.38  | 0.009     | 0.012 | 0.015 |
| C                                             | 0.15        | 0.20  | 0.25  | 0.006     | 0.008 | 0.010 | 0.15        | 0.20  | 0.25  | 0.006     | 0.008 | 0.010 |
| D                                             | 1.98        | 2.05  | 2.15  | 0.078     | 0.081 | 0.085 | 1.98        | 2.05  | 2.15  | 0.078     | 0.081 | 0.085 |
| D1                                            | 0.85        | 0.95  | 1.05  | 0.033     | 0.037 | 0.041 | 0.513       | 0.613 | 0.713 | 0.020     | 0.024 | 0.028 |
| D2                                            | 0.135       | 0.235 | 0.335 | 0.005     | 0.009 | 0.013 |             |       |       |           |       |       |
| E                                             | 1.98        | 2.05  | 2.15  | 0.078     | 0.081 | 0.085 | 1.98        | 2.05  | 2.15  | 0.078     | 0.081 | 0.085 |
| E1                                            | 1.40        | 1.50  | 1.60  | 0.055     | 0.059 | 0.063 | 0.85        | 0.95  | 1.05  | 0.033     | 0.037 | 0.041 |
| E2                                            | 0.345       | 0.395 | 0.445 | 0.014     | 0.016 | 0.018 |             |       |       |           |       |       |
| E3                                            | 0.425       | 0.475 | 0.525 | 0.017     | 0.019 | 0.021 |             |       |       |           |       |       |
| e                                             | 0.65 BSC    |       |       | 0.026 BSC |       |       | 0.65 BSC    |       |       | 0.026 BSC |       |       |
| K                                             | 0.275 TYP   |       |       | 0.011 TYP |       |       | 0.275 TYP   |       |       | 0.011 TYP |       |       |
| K1                                            | 0.400 TYP   |       |       | 0.016 TYP |       |       | 0.320 TYP   |       |       | 0.013 TYP |       |       |
| K2                                            | 0.240 TYP   |       |       | 0.009 TYP |       |       | 0.252 TYP   |       |       | 0.010 TYP |       |       |
| K3                                            | 0.225 TYP   |       |       | 0.009 TYP |       |       |             |       |       |           |       |       |
| K4                                            | 0.355 TYP   |       |       | 0.014 TYP |       |       |             |       |       |           |       |       |
| L                                             | 0.175       | 0.275 | 0.375 | 0.007     | 0.011 | 0.015 | 0.175       | 0.275 | 0.375 | 0.007     | 0.011 | 0.015 |
| T                                             |             |       |       |           |       |       | 0.05        | 0.10  | 0.15  | 0.002     | 0.004 | 0.006 |
| ECN: C-07431 – Rev. C, 06-Aug-07<br>DWG: 5934 |             |       |       |           |       |       |             |       |       |           |       |       |

## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

[Return to Index](#)



## Disclaimer

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**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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